

TENTATIVE TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7W34FU

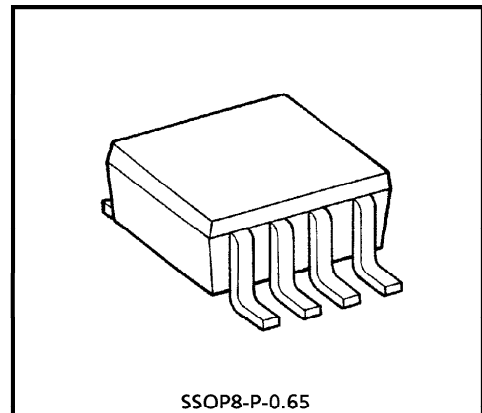
(UNDER DEVELOPMENT)

TRIPLE NON-INVERT BUFFER

The TC7W34FU is high speed CMOS BUFFER fabricated with silicon gate CMOS technology.

The internal circuit is composed of 2 stage including buffer output, which enable high noise immunity and stable output.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.



SSOP8-P-0.65

Weight : 0.02g (Typ.)

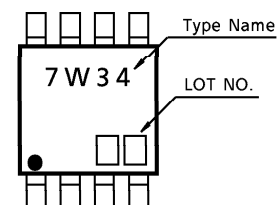
FEATURES

- High Speed $t_{pd} = 6\text{ns}$ (Typ.) at $V_{CC} = 5\text{V}$
- Low Power Dissipation $I_{CC} = 1\mu\text{A}$ (Max.) at $T_a = 25^\circ\text{C}$
- High Noise Immunity $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (Min.)
- Output Drive Capability 10 LSTTL Loads
- Symmetrical Output Impedance... $|I_{OH}| = I_{OL} = 4\text{mA}$ (Min.)
- Balanced Propagation Delays..... $t_{pLH} = t_{pHL}$
- Wide Operating Voltage Range... $V_{CC}(\text{opr}) = 2\sim 6\text{V}$

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	V_{CC}	-0.5~7	V
DC Input Voltage	V_{IN}	-0.5~ $V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	-0.5~ $V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 25	mA
DC V_{CC} /Ground Current	I_{CC}	± 25	mA
Power Dissipation	P_D	300	mW
Storage Temperature	T_{stg}	-65~150	$^\circ\text{C}$
Lead Temperature (10 s)	T_L	260	$^\circ\text{C}$

MARKING



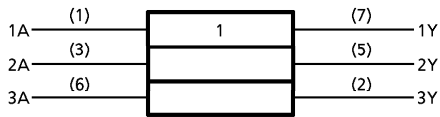
TRUTH TABLE

A	Y
L	L
H	H

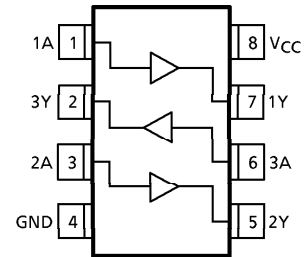
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LOGIC DIAGRAM



PIN ASSIGNMENT (TOP VIEW)



RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	V_{CC}	2~6	V
Input Voltage	V_{IN}	0~ V_{CC}	V
Output Voltage	V_{OUT}	0~ V_{CC}	V
Operating Temperature	T_{opr}	-40~85	°C
Input Rise and Fall Time	t_r, t_f	0~1000 ($V_{CC} = 2.0V$)	ns
		0~500 ($V_{CC} = 4.5V$)	
		0~400 ($V_{CC} = 6.0V$)	

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION	$T_a = 25^\circ C$			$T_a = -40 \sim 85^\circ C$		UNIT											
			V_{CC}	MIN.	TYP.	MAX.	MIN.		MAX.										
High-Level Input Voltage	V_{IH}		2.0	1.5	—	—	1.5	—	V										
			4.5	3.15	—	—	3.15	—											
			6.0	4.2	—	—	4.2	—											
Low-Level Input Voltage	V_{IL}		2.0	—	—	0.5	—	0.5	V										
			4.5	—	—	1.35	—	1.35											
			6.0	—	—	1.8	—	1.8											
High-Level Output Voltage	V_{OH}	$V_{IN} = V_{IH}$	$I_{OH} = -20 \mu A$	2.0	1.9	2.0	—	1.9	—	V									
				4.5	4.4	4.5	—	4.4	—										
				6.0	5.9	6.0	—	5.9	—										
Low-Level Output Voltage	V_{OL}	$V_{IN} = V_{IL}$	$I_{OL} = 20 \mu A$	2.0	—	0.0	0.1	—	0.1	V									
				4.5	—	0.0	0.1	—	0.1										
				6.0	—	0.0	0.1	—	0.1										
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	± 0.1	—	± 1.0	μA										
										Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	1.0	—	10.0	μA

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AC ELECTRICAL CHARACTERISTICS ($C_L = 15\text{pF}$, $V_{CC} = 5\text{V}$, $T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	Ta = 25°C			UNIT
			MIN.	TYP.	MAX.	
Output Transition Time	t_{TLH} t_{THL}	—	—	4	8	ns
Propagation Delay Time	t_{pLH} t_{pHL}	—	—	6	12	ns

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, Input $t_r = t_f = 6\text{ns}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	VCC	Ta = 25°C			Ta = -40~85°C		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition Time	t_{TLH} t_{THL}	—	2.0	—	30	75	—	95	ns
			4.5	—	8	15	—	19	
			6.0	—	7	13	—	16	
Propagation Delay Time	t_{pLH} t_{pHL}	—	2.0	—	27	75	—	95	ns
			4.5	—	9	15	—	19	
			6.0	—	8	13	—	16	
Input Capacitance	C_{IN}	—	—	5	10	—	10	pF	
Power Dissipation Capacitance	C_{PD}	(Note 1)	—	20	—	—	—	pF	

(Note 1) : C_{PD} is defined as the value of the internal equivalent capacitance of IC which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation hereunder.

$$I_{CC(opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 3 \text{ (per gate)}$$

SWITCHING CHARACTERISTICS TEST CIRCUIT

